L Number	Hits			Time stamp
1	652	257/415.ccls.	USPAT;	2003/11/14 14:05
1			US-PGPUB; EPO; JPO;	
			DERWENT;	
		257/410 1	IBM_TDB	0000/11/14 14 05
2	585	257/419.ccls.	USPAT;	2003/11/14 14:05
į			EPO; JPO;	
			DERWENT;	
3	38	i 257/424.ccls.	IBM_TDB   USPAT;	2003/11/14 14:05
			US-PGPUB;	2.003/11/14 11.03
			EPO; JPO;	
	}		DERWENT; IBM TDB	
_	161	257/254.ccls.	USPĀT;	2003/02/05 16:14
]			US-PGPUB;	
	İ		EPO; JPO; DERWENT;	
			IBM TDB	
-	9	(201,201,0020, 4114 (9400 116410 011140), 4114	USPĀT;	2003/02/05 16:12
		acceleration	US-PGPUB; EPO; JPO;	
			DERWENT;	
	}		IBM_TDB	
-	2	· · · · · · · · · · · · · · · ·	USPAT;	2003/02/05 16:12
		and acceleration) and spring	US-PGPUB; EPO; JPO;	
			DERWENT;	
	10	257/254 colo and coolematica and coolema	TBM_TDB	2003/02/05 16:15
-	]	257/254.ccls. and acceleration and spring	USPAT; US-PGPUB;	2003/02/05 16:15
			EPO; JPO;	
l			DERWENT;	
_	8	(257/254.ccls. and acceleration and	IBM_TDB USPAT;	2003/02/05 16:19
	1	spring) not ((257/254.ccls. and (gate	US-PGPUB;	2000,02,00
i i		near3 oxide)) and acceleration)	EPO; JPO;	
			DERWENT; IBM TDB	
-	12153	acceleration same switch	USPĀT;	2003/07/30 14:48
ĺ			US-PGPUB;	
}	}		EPO; JPO; DERWENT;	
1	}		IBM_TDB	
-	21.		USPĀT;	2003/11/12 18:45
		near5 (oxide or insulator)) and (drain or source))	US-PGPUB; EPO; JPO;	
,			DERWENT;	
	1.1	//acanlamatian name assistable and //aci	IBM_TDB	2002/02/05 16 03
-	11	((acceleration same switch) and ((gate near5 (oxide or insulator)) and (drain or	USPAT; US-PGPUB;	2003/02/05 16:21
	ļ	source))) and spring	EPO; JPO;	
	ļ		DERWENT;	
_	24	(acceleration same switch) and (gate near5	IBM TDB USPAT;	2003/02/05 16:22
	[	(oxide or insulator))	US-PGPUB;	
[	!		EPO; JPO;	 
}			DERWENT; IBM TDB	
-	11		USPAT;	2003/02/05 16:31
1		near5 (oxide or insulator)) ) and spring	US-PGPUB;	
}	}		EPO; JPO; DERWENT;	
			IBM_TDB	
-	363	(acceleration same switch) and gate and	USPĀT;	2003/02/05 16:57
		drain 	US-PGPUB; EPO; JPO;	
1			DERWENT;	
L '	<u>                                       </u>	<u></u>	IBM_TDB	)

·		<del>,</del> - : <del></del>		
	330	((acceleration same switch) and gate and drain) and source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 16:58
_	312	(((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator)) )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 16:59
-	0	<pre>((((((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator)))) and spring) not (((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator))))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 17:44
	183	<pre>((((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator)) )) not ((((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator)) )) and spring)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/05 17:52
-	1.60	257/254.ccls. not ((acceleration same switch) and (gate near5 (oxide or insulator)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/05 17:53
-	15	(257/254.ccls. and (gate near3 oxide)) not ((((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator)) ))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 17:53
-	5		USPA'T	2003/02/06 13:00
-	5	(US-5619050-\$ or US-5504356-\$ or US-5922212-\$ or US-6388299-\$ or US-5812427-\$).did.	USPAT	2003/02/06 12:58
-	5	(US-5619050-\$ or US-5504356-\$ or US-5922212-\$ or US-6388299-\$ or US-5812427-\$).did.	USPAT	2003/02/06 12:58
-		("5619050").PN.   ((US-5619050-\$ or US-5504356-\$ or   US-5922212-\$ or US-6388299-\$ or   US-5812427-\$).did.) and (silicon near	USPAT USPAT	2003/02/06 12:59 2003/02/06 13:03
-	1	dioxide)   ((US-5619050-\$ or US-5504356-\$ or   US-5922212-\$ or US-6388299-\$ or   US-5812427-\$).did.) and (silicon near   dioxide)	USPAT	2003/02/06 13:03
	13		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/06 13:05
-	0	<pre>(((acceleration same switch) and (gate near5 (oxide or insulator)) ) not (((acceleration same switch) and (gate near5 (oxide or insulator)) ) and spring)) and (silicon near3 dioxide)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/06 13:05
_	15	257/254.ccls. and (gate near3 oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/06 13:05

[ -	4	(257/254.ccls. and (gate near3 oxide)) and (silicon near3 dioxide)	USPAT; US-PGPUB; EPO; JPO;	2003/07/30 15:29
\ 			DERWENT;	
Ì -	129		USPĀT;	2003/02/06 13:10
		drain) and source) not ((acceleration same switch) and (gate near5 (oxide or	US-PGPUB; EPO; JPO;	
		insulator)) )) and spring	DERWENT;	į
_	0		IBM_TDR USPAT;	2003/02/06 13:11
		and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or	US-PGPUB; EPO; JPO;	
		insulator)) )) and spring) and (silicon	DERWENT;	
_	1	near3 oxide) (((((acceleration same switch) and gate	IBM_TDB USPAT;	2003/02/06 13:11
		and drain) and source) not ((acceleration	US-PGPUB;	2.003/02/00 13:11
		same switch) and (gate near5 (oxide or insulator)) )) and spring) and (silicon	EPO; JPO; DERWENT;	
		near3 dioxide)	IBM_TDB	
_	238	73/514.36.ccls.	USPAT; US-PGPUB;	2003/02/06 13:11
			EPO; JPO;	
			DERWENT; IBM TDB	
<del>-</del>	193		USPĀT;	2003/02/06 13:12
		prossure)	US-PGPUB; EPO; JPO;	
	ļ		DERWENT;	
_	4	(73/514.36.ccls. and (acceleration or	IBM_TDB USPAT;	2003/02/06 13:12
		pressure)) and gate and (silicon near3 dioxide)	US-PGPUB; EPO; JPO;	
		dioxide	DERWENT;	
_	1	("5627397").PN.	IBM_TDB USPAT	2003/02/06 14:34
_	2190	(acceleration same switch) and	USPAT;	2003/07/30 14:50
		(semiconductor or ic or (integrated near2 circuit) or chip or die)	US-PGPUB; EPO; JPO;	1
			DERWENT; IBM TDB	
_	1458	, ,	USPĀT;	2003/11/12 18:34
	į	(semiconductor or ic or (integrated near2 circuit) or chip or die)) and (source or	US-PGPUB; EPO; JPO;	
		drain)	DERWENT;	
_	   167	   257/254.ccls.	IBM_TDB USPAT;	2003/07/30 15:29
	 		US-PGPUB;	
			EPO; JPO; DERWENT;	
_	 i 818	257/417.ccls.	IBM_TDB USPAT;	2003/07/30 15:29
		,	US-PGPUB;	2000,0,,50 10.29
			EPO; JPO; DERWENT;	
		257/410	IBM_TDB	0000 /011 /30 15 00
_	243	257/418.ccls.	USPAT; US-PGPUB;	2003/07/30 15:30
			EPO; JPO;	
			DERWENT; IBM_TDB	
-	157	257/420.ccls.	USPAT; US-PGPUB;	2003/11/14 14:05
	ļ		EPO; JPO;	
			DERWENT; IBM TDB	
-	103	73/514.21.ccls.	USPAT;	2003/07/30 15:30
			US-PGPUB; EPO; JPO;	
ļ			DERWENT;	
i		L	IBM TDB	

-	1508	((acceleration same switch) and	USPAT;	2003/11/12 18:35
		(semiconductor or ic or (integrated near2	US-PGPUB;	
	ĺ	circuit) or chip or die)) and (source or	EPO; JPO;	
İ		drain)	DERWENT;	
1			IBM_TDB	[
-	26	(acceleration same switch) and ((gate	USPAT;	2003/11/12 18:45
(	Į	near5 (oxide or insulator)) and (drain or	US-PGPUB;	{
-		source))	EPO; JPO;	
	į		DERWENT;	
	<u> </u>		IBM TDB	